

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.

08228.021001

SERIAL NO.

Shiro SAKAI

FILING

March 6, 2002

GROUP

J1046 U.S. PT

10/092231

03/06/02

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	A1	6,030,848	02/29/2000	Yuge et al.	438	46	04/16/1997
	A2	5,929,466	07/27/1999	Ohba et al.	257	103	06/13/1997
	A3	5,900,650	05/04/1999	Nitta	257	94	07/02/1997
	A4	5,888,886	03/30/1999	Sverdlov et al.	438	505	06/30/1997
	A5	6,177,684B1	01/23/2001	Sugiyama	257	17	07/29/1998

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
JN	A6	10-312971	11/24/1998	Japan	H01L	21/205		✓
	A7	2000-21789	01/21/2000	Japan	H01L	21/205		✓
	A8	11-354839	12/24/1999	Japan	H01L	33/00		✓
	A9	11-354840	12/24/1999	Japan	H01L	33/00		✓
	A10	11-354842	12/24/1999	Japan	H01L	33/00		✓

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JN	A11	English/Japanese Notice of Grounds For Rejection, Japanese Patent Application Serial No. 2000-227963, 7 pages					
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
JN	B1	11-266004	09/28/1999	Japan	H01L	29/06		✓
	B2	9-227298	09/02/1997	Japan	C30B	29/38		✓
	B3	10-22568	01/23/1998	Japan	H01S	3/18		✓
	B4	11-135832	05/21/1999	Japan	H01L	33/00		✓
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							YES	NO
JN	C1	11-145516	05/28/1999	Japan	H01L	33/00		✓
	C2	11-346032	12/14/1999	Japan	H01S	3/18		✓
	C3	11-346035	12/14/1999	Japan	H01S	3/18		✓
	C4	2000-91252	03/31/2000	Japan	H01L	21/205		✓
	C5	2000-91253	03/31/2000	Japan	H01L	21/205		✓

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							YES	NO
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# INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

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Application Number

Applicant(s)

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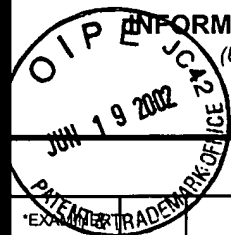
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2811

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	A5	11-111867	04/23/1999	Japan	H01L	21/8247		

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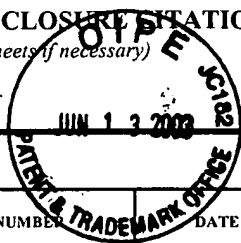
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							YES	NO
JN	A1	4-288871	08/03/1993	Japan	HO1L	21/469		✓
	A2	9-17975	01/17/1997	Japan	HO1L	27/108		✓
	A3	10-163525	06/19/1998	Japan	HO1L	33/00		✓
	A4	EP 0 961 328 A2	12/01/1999	Europe	HO1L	33/00		

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	A6	Japanese Patent Application Serial No. 2000-289103 Office Action dated April 22, 2003.

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